

ZXMP10A18G

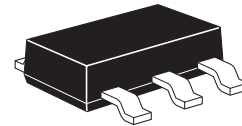
100V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = -100V$; $R_{DS(on)} = 0.150\Omega$; $I_D = -3.7A$

DESCRIPTION

This new generation of Trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



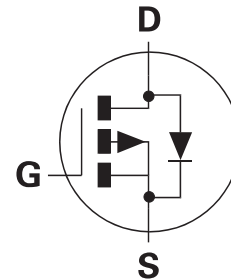
SOT223

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT223 package

APPLICATIONS

- DC-DC Converters
- Power Management functions
- Relay and Solenoid driving
- Motor control



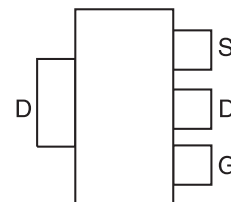
ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMP10A18GTA	7"	12mm	1,000 units
ZXMP10A18GTC	13"	12mm	4,000 units

DEVICE MARKING

- ZXMP
10A18

PINOUT



ZXMP10A18G

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current @ $V_{GS}=10V$; $T_A=25^\circ C$ ^(b)	I_D	-3.7	A
@ $V_{GS}=10V$; $T_A=70^\circ C$ ^(b)		-3.0	A
@ $V_{GS}=10V$; $T_A=25^\circ C$ ^(a)		-2.6	A
Pulsed Drain Current ^(c)	I_{DM}	-16.5	A
Continuous Source Current (Body Diode) ^(b)	I_S	-5.3	A
Pulsed Source Current (Body Diode) ^(c)	I_{SM}	-16.5	A
Power Dissipation at $T_A=25^\circ C$ ^(a)	P_D	2	W
Linear Derating Factor		16	mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ ^(b)	P_D	3.9	W
Linear Derating Factor		31	mW/ $^\circ C$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient ^(a)	$R_{\theta JA}$	62.5	$^\circ C/W$
Junction to Ambient ^(b)	$R_{\theta JA}$	32.2	$^\circ C/W$

NOTES

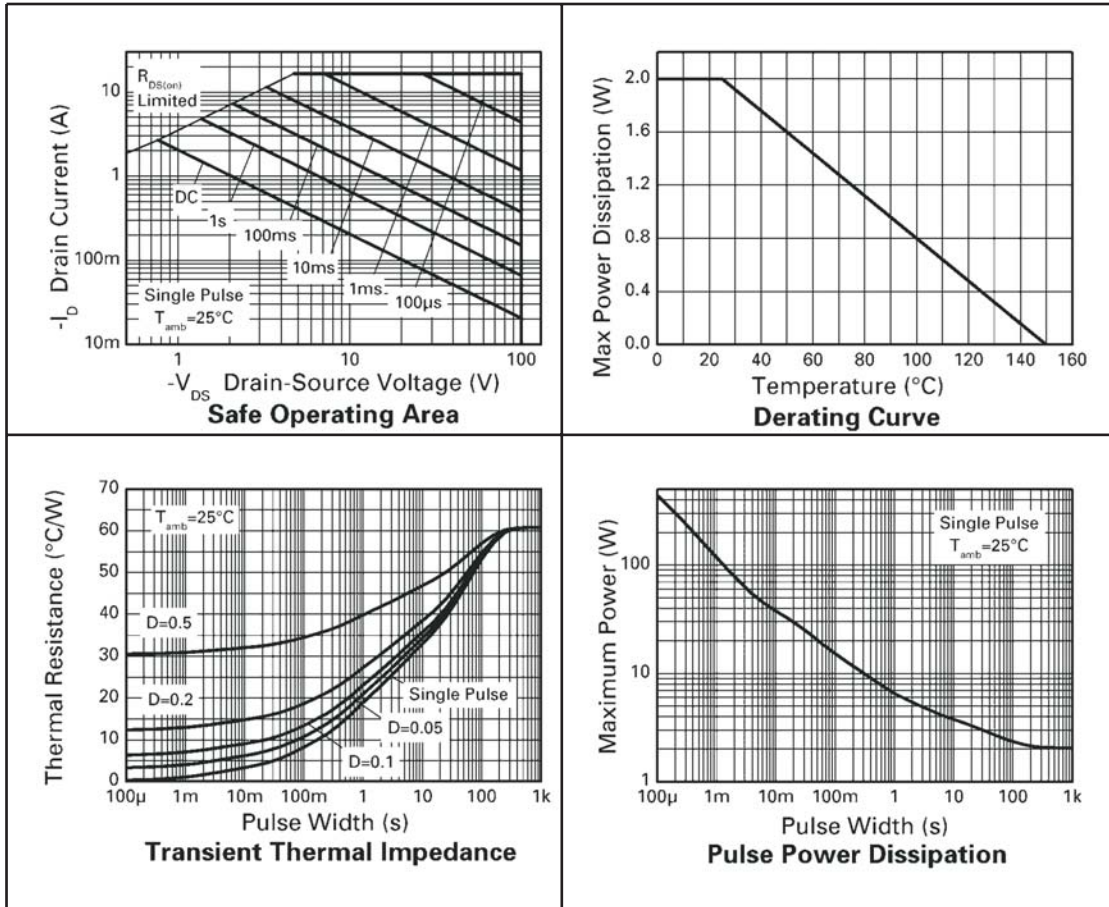
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ sec.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.02$ pulse width = 300 μs - pulse width limited by maximum junction temperature.

ZXMP10A18G

CHARACTERISTICS



ZXMP10A18G

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

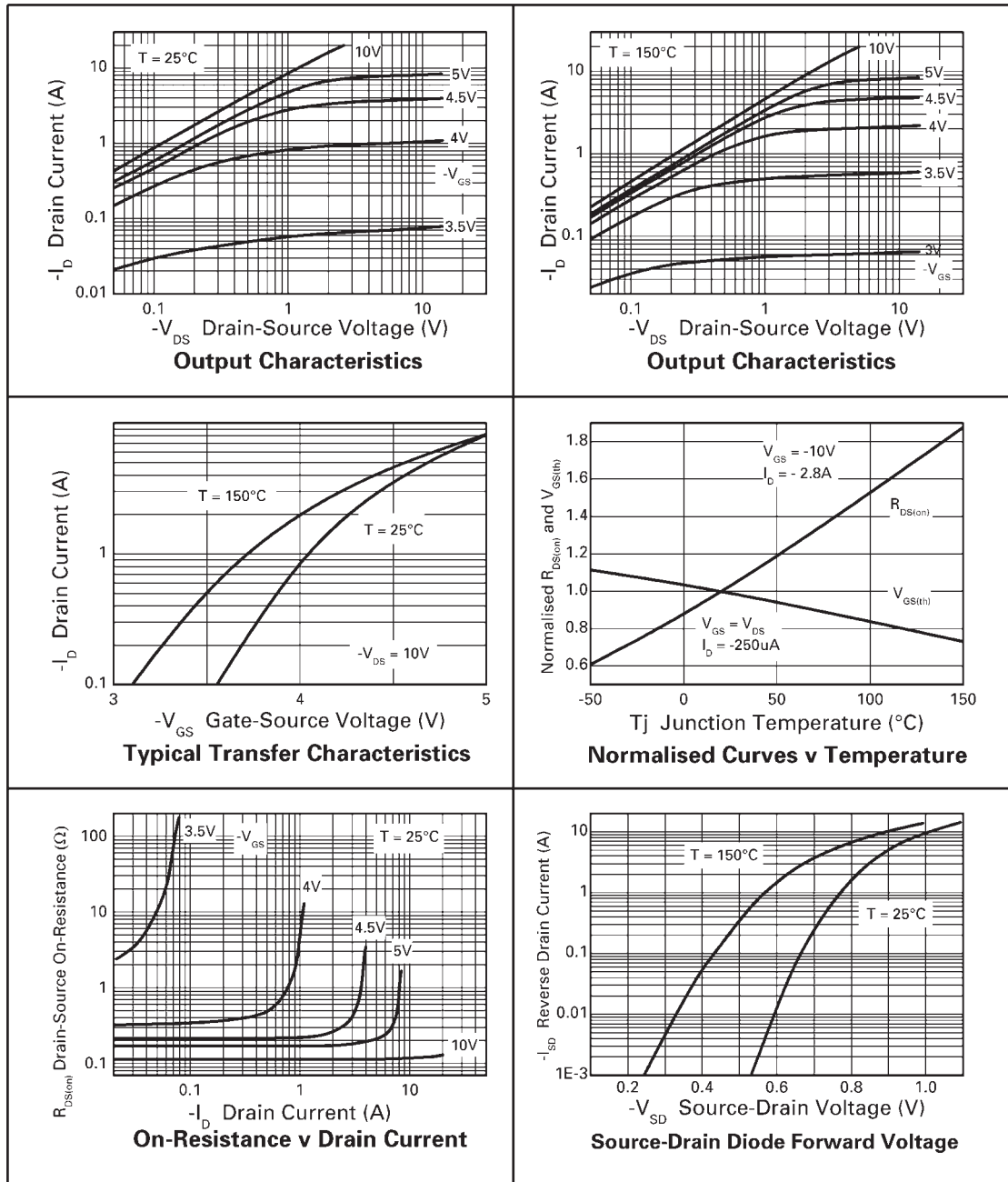
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-100			V	I _D = -250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			-1	μA	V _{DS} = -100V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	-2.0		-4.0	V	I _D = -250μA, V _{DS} =V _{GS}
Static Drain-Source On-State Resistance ⁽¹⁾	R _{DS(on)}			0.150	Ω	V _{GS} = -10V, I _D = -2.8A
				0.190	Ω	V _{GS} = -6V, I _D = -2.4A
Forward Transconductance ⁽¹⁾⁽³⁾	g _{fs}		6.0		S	V _{DS} = -15V, I _D = -2.8A
DYNAMIC ⁽³⁾						
Input Capacitance	C _{iss}		1055		pF	V _{DS} = -50V, V _{GS} =0V f=1MHz
Output Capacitance	C _{oss}		90		pF	
Reverse Transfer Capacitance	C _{rss}		76		pF	
SWITCHING ^{(2) (3)}						
Turn-On Delay Time	t _{d(on)}		4.6		ns	V _{DD} = -50V, I _D = -1A R _G = 6.0Ω, V _{GS} = -10V
Rise Time	t _r		6.8		ns	
Turn-Off Delay Time	t _{d(off)}		33.9		ns	
Fall Time	t _f		17.9		ns	
Total Gate Charge	Q _g		26.9		nC	V _{DS} = -50V, V _{GS} = -10V I _D = -2.8A
Gate-Source Charge	Q _{gs}		3.9		nC	
Gate-Drain Charge	Q _{gd}		10.2		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage ⁽¹⁾	V _{SD}		-0.85	-0.95	V	T _j =25°C, I _S = -3.5A, V _{GS} =0V
Reverse Recovery Time ⁽³⁾	t _{rr}		49		ns	T _j =25°C, I _S = -2.8A,
Reverse Recovery Charge ⁽³⁾	Q _{rr}		107		nC	di/dt=100A/μs

NOTES

- (1) Measured under pulsed conditions. Pulse width $\leq 300\text{ms}$; duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

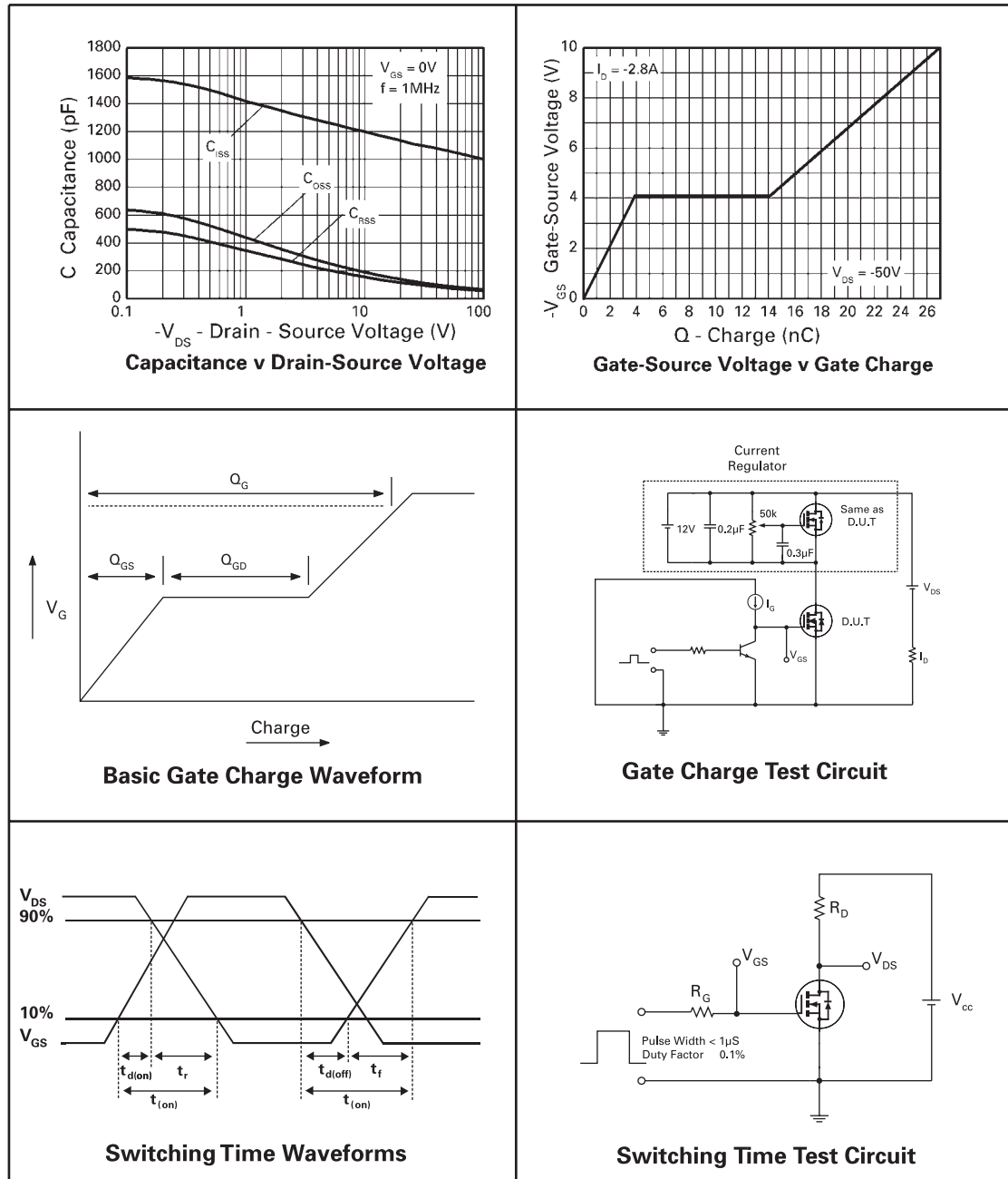
ZXMP10A18G

TYPICAL CHARACTERISTICS



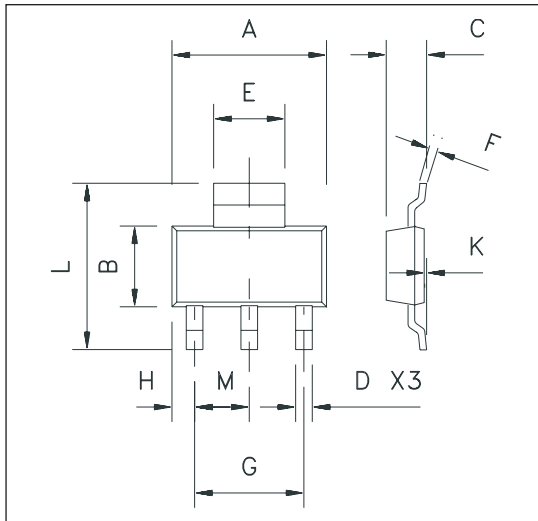
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TYPICAL CHARACTERISTICS

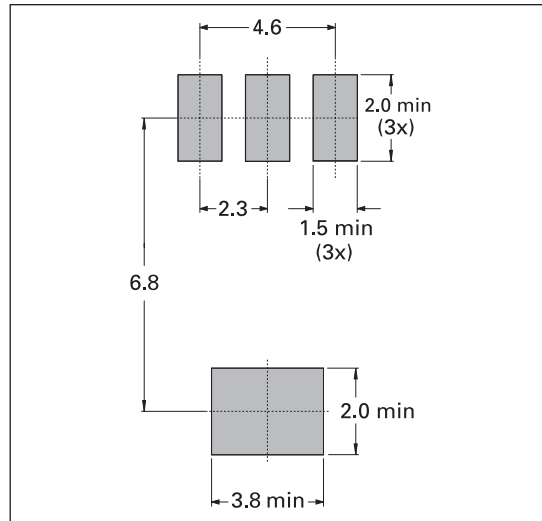


ZXMP10A18G

PACKAGE OUTLINE



PAD LAYOUT DETAILS



Controlling dimensions are in millimetres. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millimetres		Inches		DIM	Millimetres		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	6.3	6.7	0.248	0.264	G	NOM 4.6		NOM 0.181	
B	3.3	3.7	0.130	0.146	H	0.85	1.05	0.033	0.041
C	-	1.7	-	0.067	K	0.02	0.10	0.0008	0.004
D	0.6	0.8	0.024	0.031	L	6.7	7.3	0.264	0.287
E	2.9	3.1	0.114	0.122	M	NOM 2.3		NOM 0.0905	
F	0.24	0.32	0.009	0.13					

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